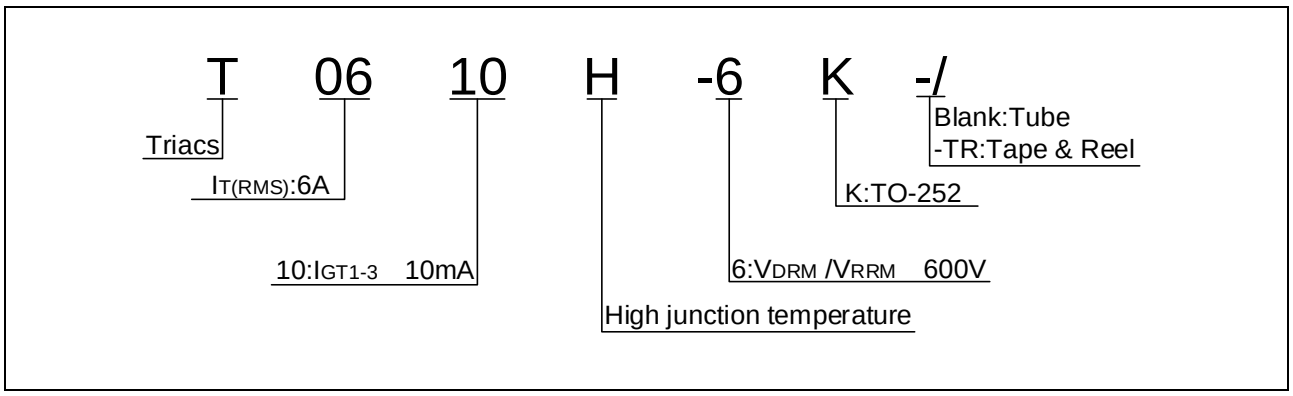
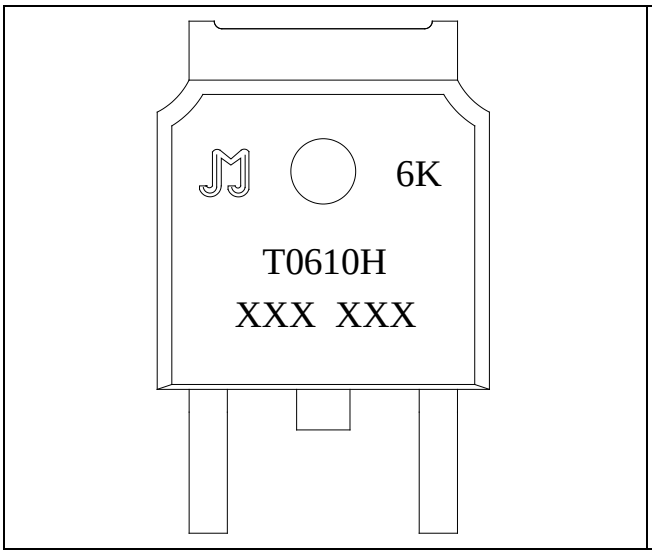
Peak gate power		P_{GM}	10	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.8)		V_{pp}	3	kV

(T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value	Unit
I_{GT}	V_D =12V R_L =33Ω	- -	MAX. 10	


T 06 10 H -6 K -/
Triacs
IT(RMS):6A
10:IGT1-3 10mA
High junction temperature
6:VDRM /VRRM 600V
K:TO-252
Blank:Tube
-TR:Tape & Reel


6K
T0610H
XXX XXX

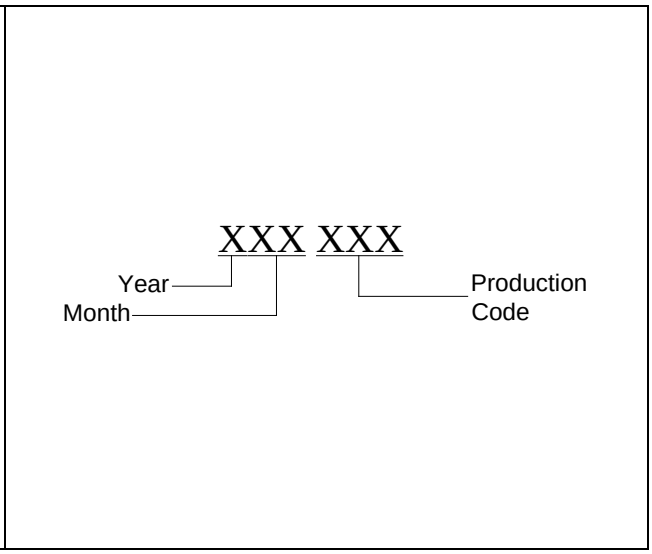

XXX XXX
Year
Month
Production
Code

FIG.1: Maximum power dissipation versus RMS on-state current



FIG.2: RMS on-state current versus case temperature

FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

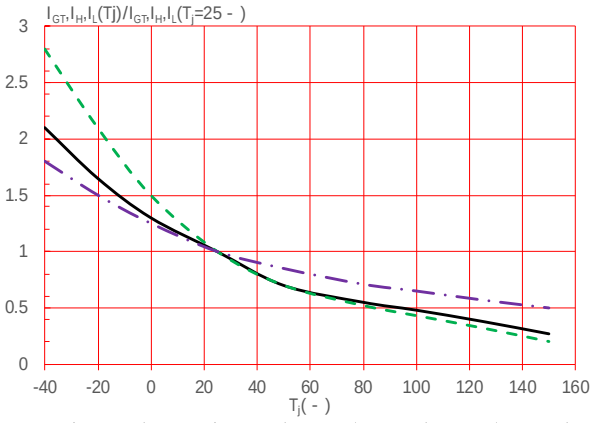
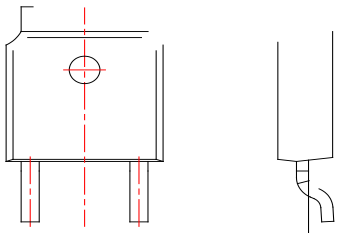


FIG.8 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards





Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.15	0		0.006
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1						
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
G1	2.18		2.38	0.086		0.094
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065



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